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( Not for submission under 37 CFR 1.99)

Application Number	10632882
Filing Date	2003-07-31
First Named Inventor	Gopalraja
Art Unit	1753
Examiner Name	Rodney Glenn McDonald
Attorney Docket Number	06775USA

**U.S.PATENTS**


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/RM/	1	6080285		2000-06-27	Liu	
/RM/	2	6110821		2000-08-29	Kohara	
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/RM/	1	20050252765		2005-11-17	Zhang	
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<b>U.S. PATENT DOCUMENTS</b>						
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<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>						
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